

CCD-based Pixel Detectors by LCFI

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SiD workshop, Fermilab April 2007

Outline

- CCD Sensors and Readout
 - ◆ Column-Parallel CCDs
 - ◆ Storage Pixels : ISIS

- Mechanical Studies

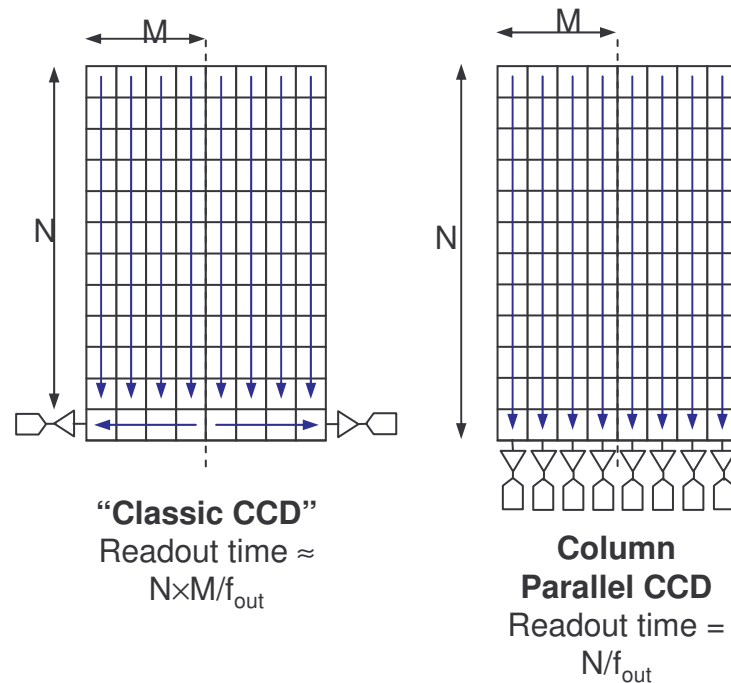
Column Parallel CCD

- Simple idea : read out a vector instead of a matrix \rightarrow Readout time shortened by orders of magnitude

BUT

- Every column needs own amplifier and ADC \rightarrow requires readout chip
- Need to operate at 50 MHz to meet readout rate spec \rightarrow 20 Amp clock current

Driving of CPCCD is a major challenge

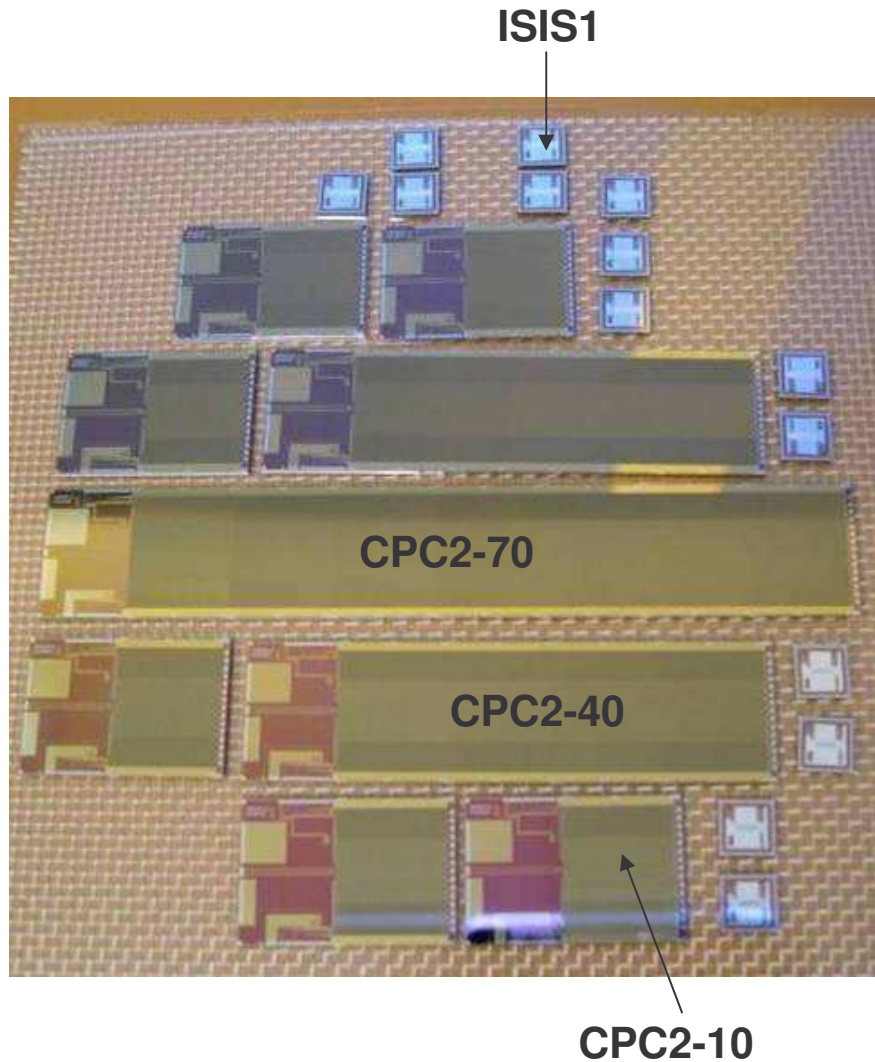


- Voltage drops $20 \text{ A} \times 0.1 \text{ Ohm} = 2 \text{ V}$
- Inductance of 1mm long bond wire = 1 nH, corresponds to 0.3 Ohm at 50 MHz

CPCCD : LCFI R&D Milestones

- Established proof of principle for small area sensors : CPC1
- Established proof of principle for readout chip : CPR1, developed and produced more sophisticated CPR2
- Moved on to large area sensors : CPC2
 - ◆ Produced and tested busline free high speed CPC2
 - ◆ Testing of CPC2/CPR2 assemblies
 - ◆ Need to handle the problem of clock driver
 1. Design dedicated clock driver : CPD1
 2. Find ways to reduce the CCD capacitance
 3. Find ways to reduce the required clock voltage

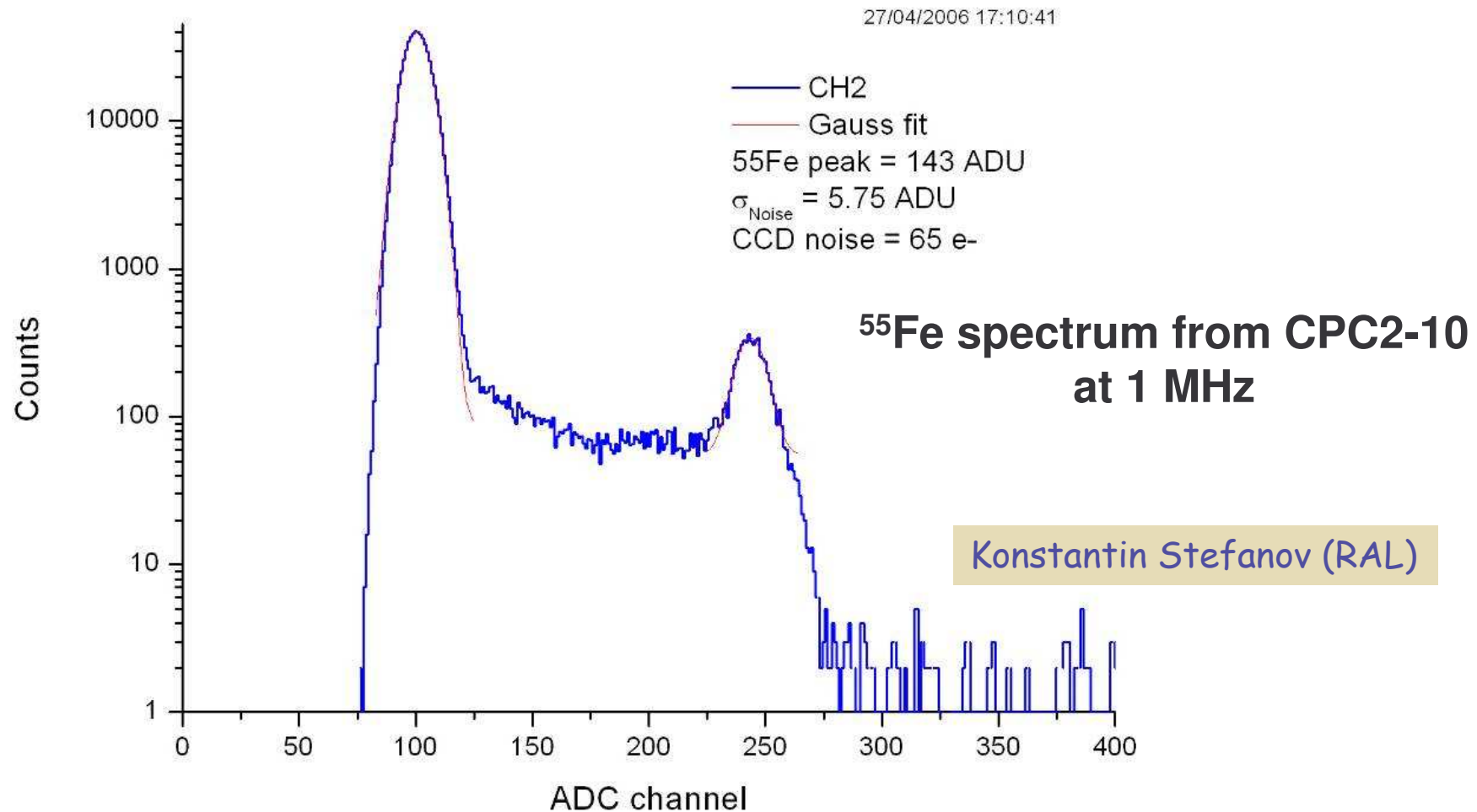
Second Generation CPCCD : CPC2



- 6 wafers with single level metal:
 - Four CPC2 wafers ($3 \times 100 \Omega\text{.cm}/25 \mu\text{m}$ epi and one $1.5\text{k}\Omega\text{.cm}/50 \mu\text{m}$ epi)
 - Two $100 \Omega\text{.cm}$ wafers bump bonded at VTT to CPR2 readout chip
- 2 CPC2 wafers with 2-level metal (busline-free CCD) delivered in November 2006
 - Designed to reach 50 MHz operation
- Have another 12 wafers to be processed after evaluation of the present variants

Yield from 4 single metal CPC2 wafers: 71% for CPC2-10, 63% for CPC2-40, 25% for CPC2-70

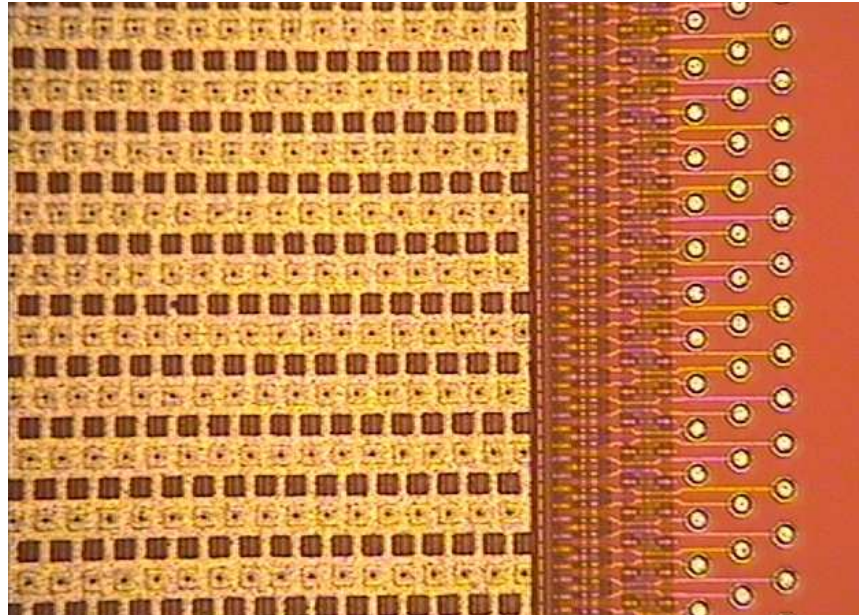
CPC2 Results at 1 MHz



- Analogue readout (no RO chip) at -40 °C
- Noise 65 e- (typical MIP signal 1600 e-)

CPC2: Double Level Metal

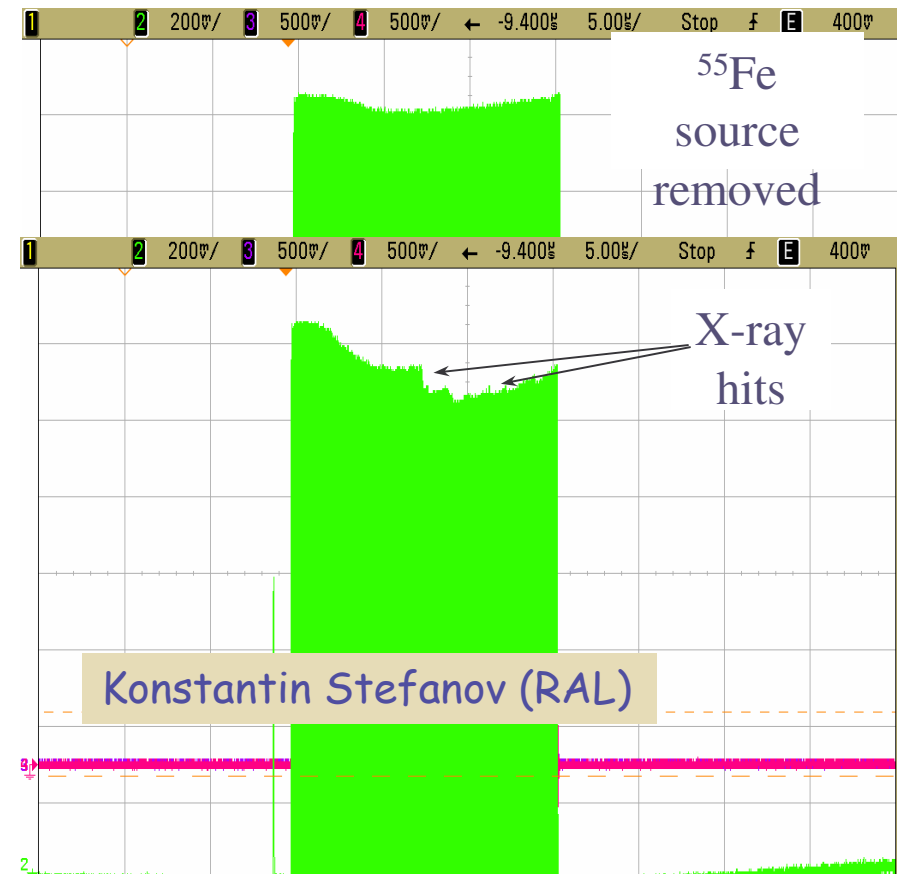
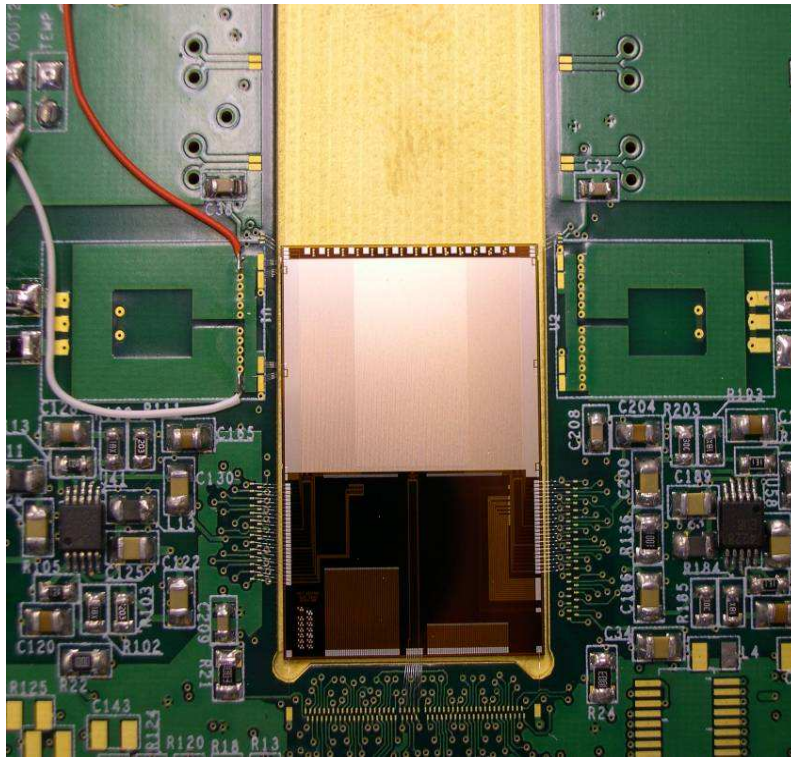
Busline-free CPC2



- Devices with 2-level metal clock distribution for high speed (busline-free) have been received
 - The whole image area serves as a distributed busline
 - Parasitic inductance is minimized but capacitance is larger by factor of ~ 2

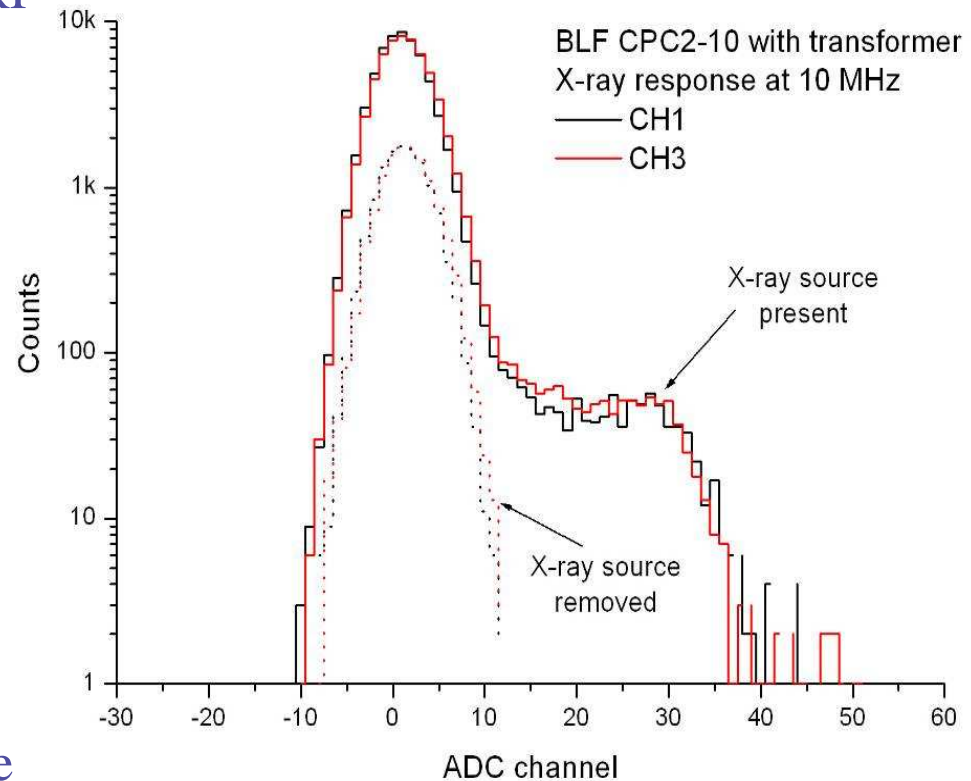
Busline Free CPC2 Testing

- CPC2-10 wire bonded to mother-board with transformer drive
- ^{55}Fe X-ray signals observed at up to 45 MHz!



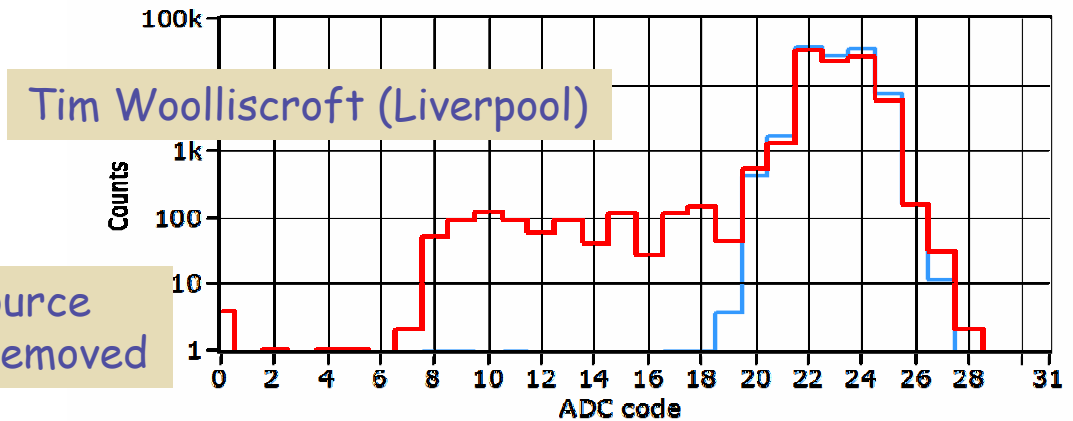
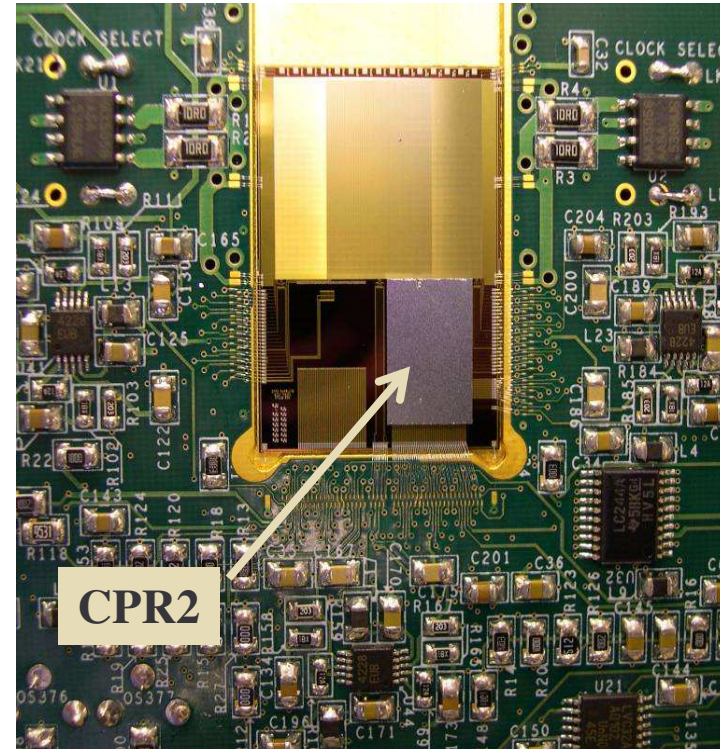
Busline Free CPC2 Tests

- Established operation at up to 45 MHz
 - ◆ Observed higher noise- due to RF amplifier used to provide clock
 - ◆ Work is in progress to improve the transformer drive circuit
- Observed efficient charge transfer with 0.4 V_{PP} clock signals
 - ◆ Expected 2 V_{PP}
 - ◆ Not a resonance effect.
 - ◆ Studying test structures from the same wafers to understand implant concentrations



CPC2 Bump Bonded to CPR2

- CPC2 and CPR2 were successfully bump bonded at VTT
- Tests started – saw first X-ray spectra
- Two assemblies died after a short period
 - ◆ Work in progress to understand this and implement more monitoring and safety features

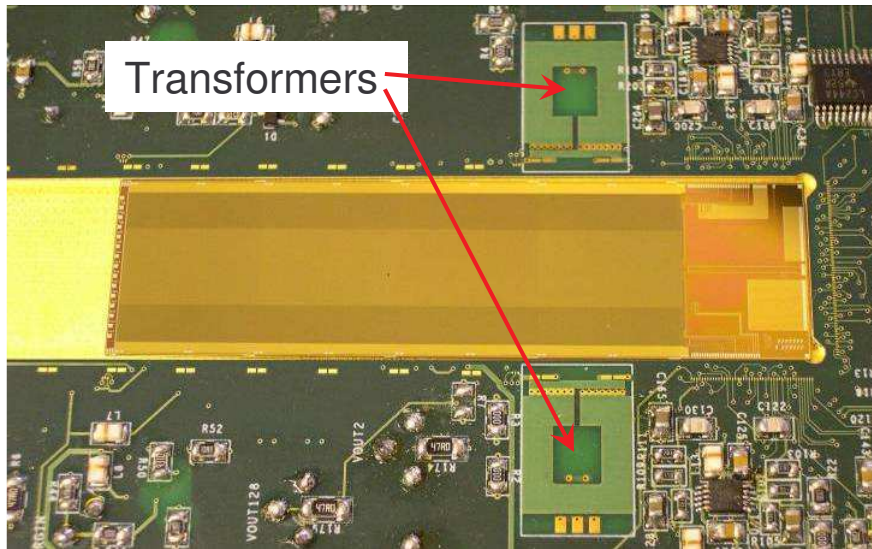


Clock Drivers for CPC2

Requirements: $2 V_{pk-pk}$ at 50 MHz over 40 nF

Transformer

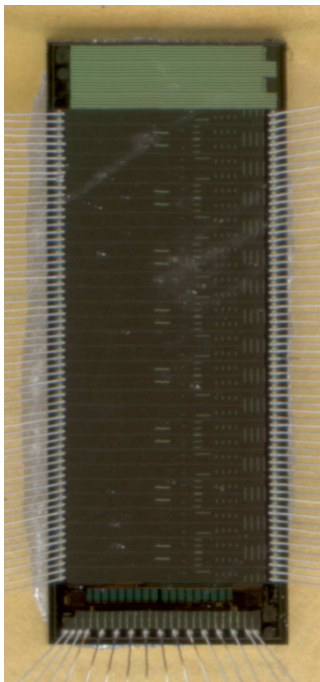
- Planar air core transformers on 10-layer PCB, size 1 cm^2
- Parasitic inductance of bond wires is a major effect
- Used to drive high speed busline-free CPC2



Johan Fopma/Brian Hawes, Oxford U

Custom clock driver: CPD1 chip

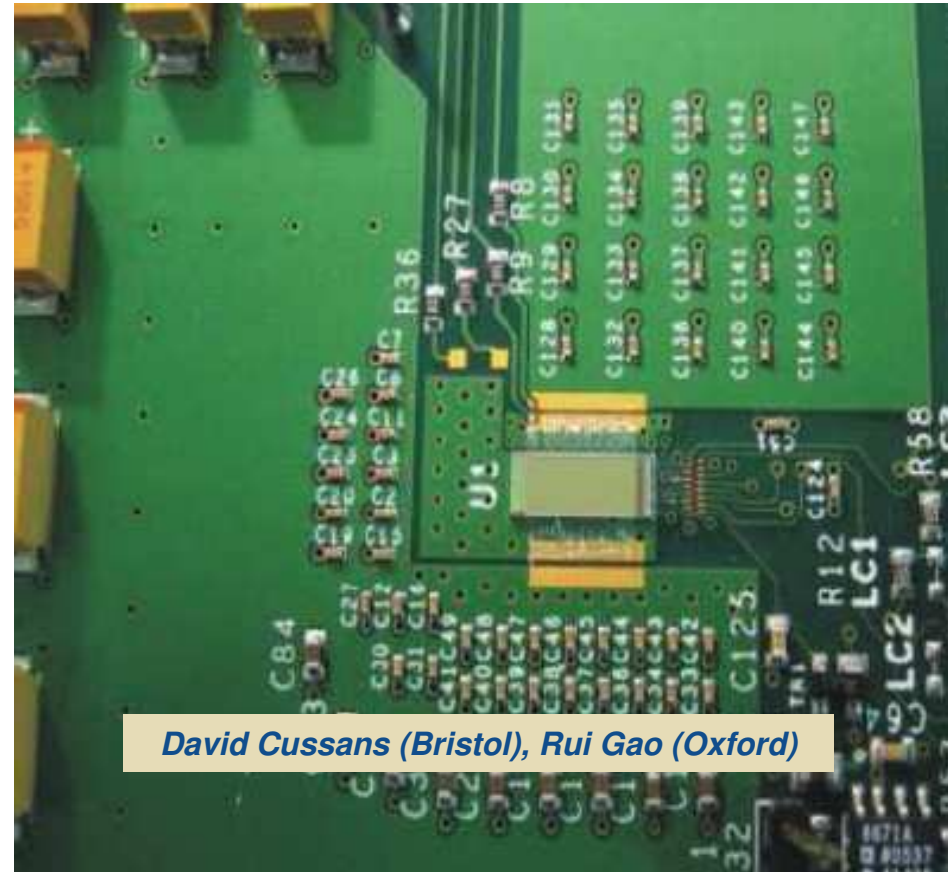
- First CPCCD driver chip (CPD1) delivered in October 2006
- Designed to drive the outer layer CCDs (127 nF/phase) at 25 MHz and the L1 CCD (40 nF/phase) at 50 MHz
- One chip drives 2 phases, 3.3 V clock swing
- 0.35 μm process, size $\approx 3 \times 8 \text{ mm}^2$
- 32 W peak power but 0.5% duty cycle
- Thermal and electromigration issues are under control



Steve Thomas/Peter Murray, RAL

CPD1 Tests

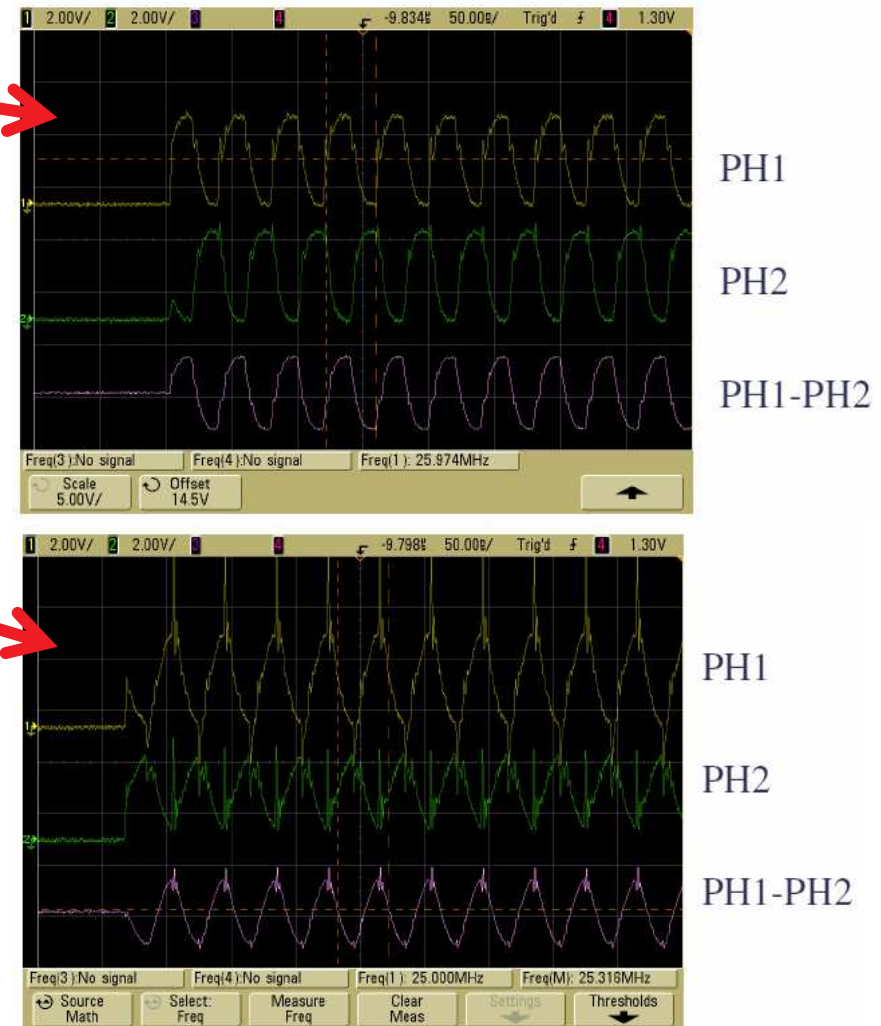
- Standalone tests of CPD1 use a dedicated board
- Test board allows to exercise various modes of operation and provides external capacitive load
- Parasitic inductance is dominated by bond wires
- CPD1 has 8 sections
 - ◆ One of the sections is connected to 2nF internal capacitor to test the performance with minimal inductance
 - ◆ Outputs have alternating PH1/PH2 pads to minimize inductance



CPD1 Results

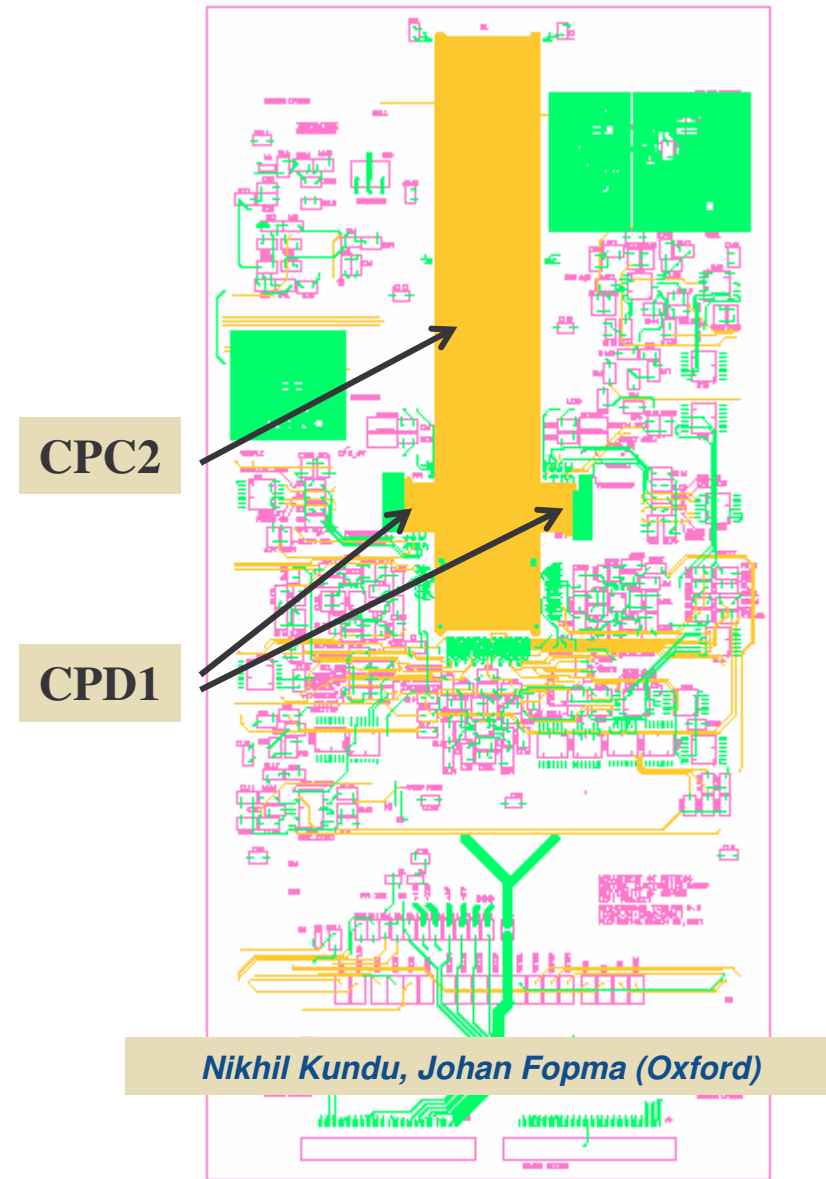
Inverter Mode, 25Mhz

- Internal 2 nF capacitor
- External 40 nF capacitor
 - ◆ Minimal deterioration of performance
- Initial tests are very promising – CPD1 is able to drive 40 nF load at 25 MHz maintaining proper pulse shape

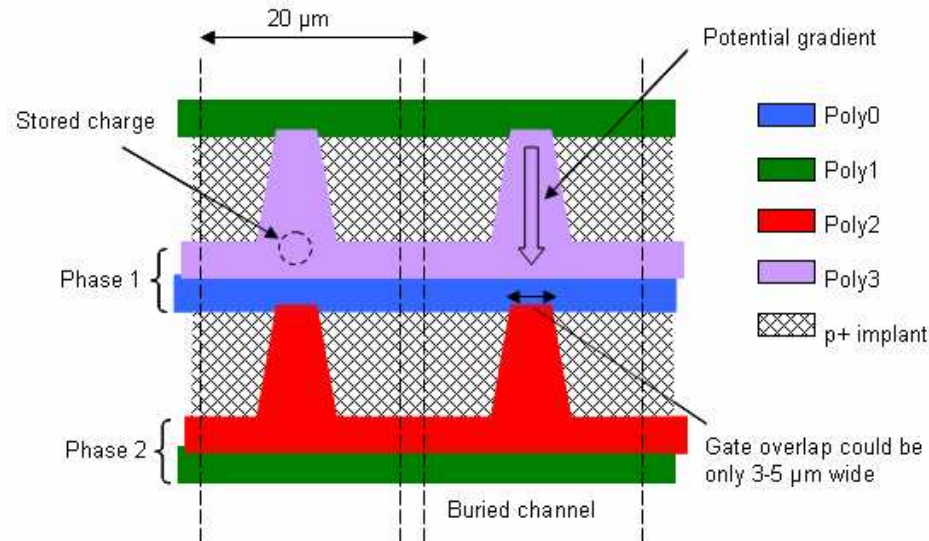


CPD1 Tests

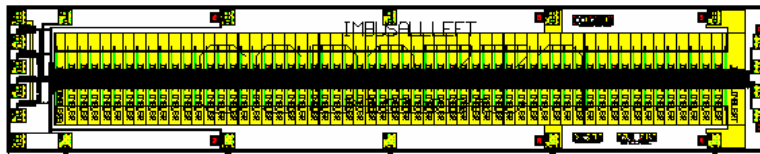
- Next step: operation of CPC2 with CPD1
- New test board in preparation
 - ◆ Two CPD1 chips will drive one CPC2
 - ◆ Need to interface CPC2 clock bonding pads to CPD1 bonding pads keeping the parasitic inductance low – will have a small adapter board between CPC2 and CPD1
- Should have results by the summer



New Ideas: CCDs for Capacitance Reduction

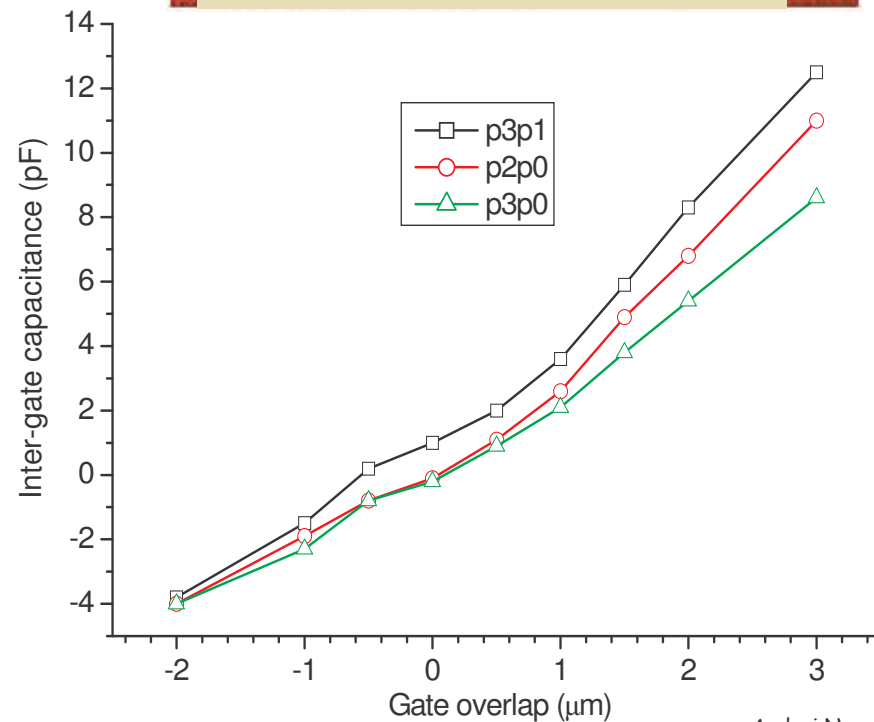
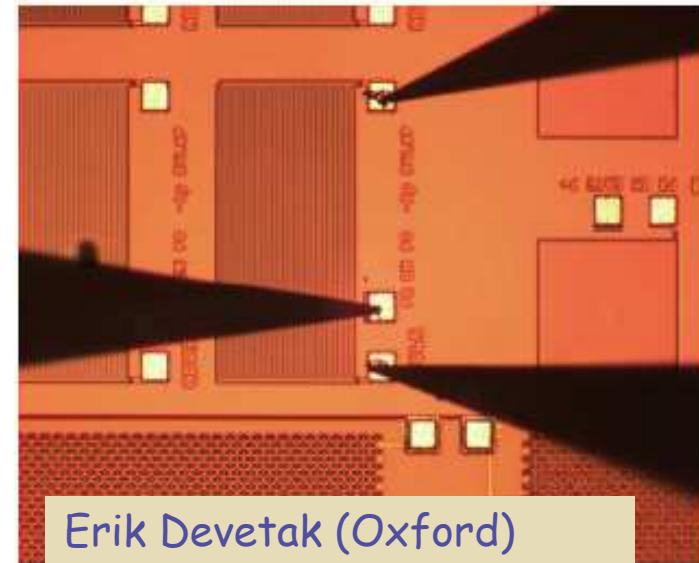


- High CCD capacitance is a challenge to drive because of the currents involved - Can we reduce the capacitance?
- Inter-gate capacitance C_{ig} is dominant, depends mostly on the size of the gaps and the gate area
- Theoretically can achieve factor of 4 reduction in C
- Prepared several designs together with e2V and ordered mini CPCCDs: 10(H)×480(V) pixels

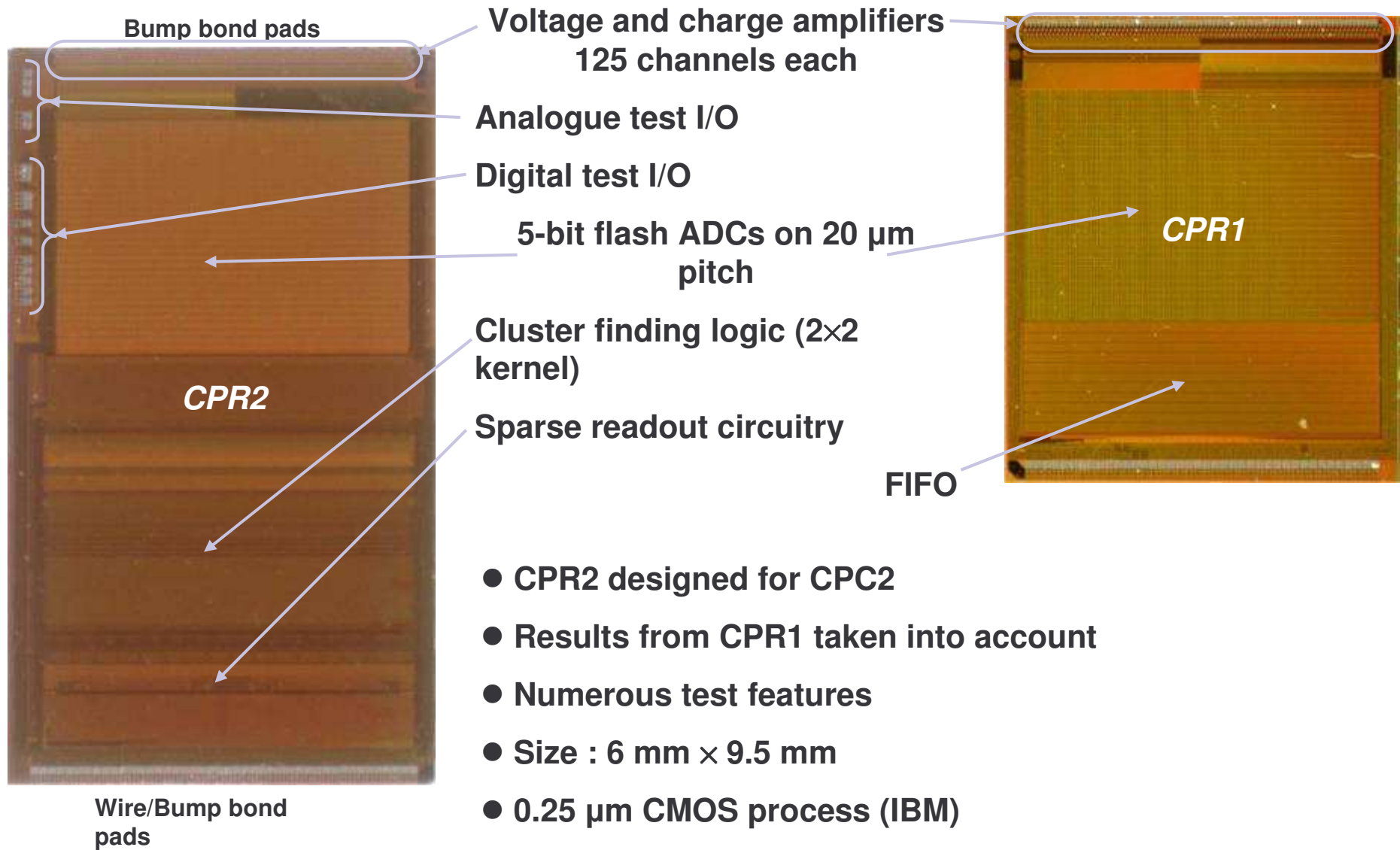


Capacitance Overlap Measurements

- Have test structures with variable overlap distance between gates
- Will provide data on relationship between design and actual inter-gate overlap
- Useful to verify simulation of intergate capacitance
- First results show evidence of non-linearity around overlap of zero
 - ◆ Absolute calibration needs to be improved



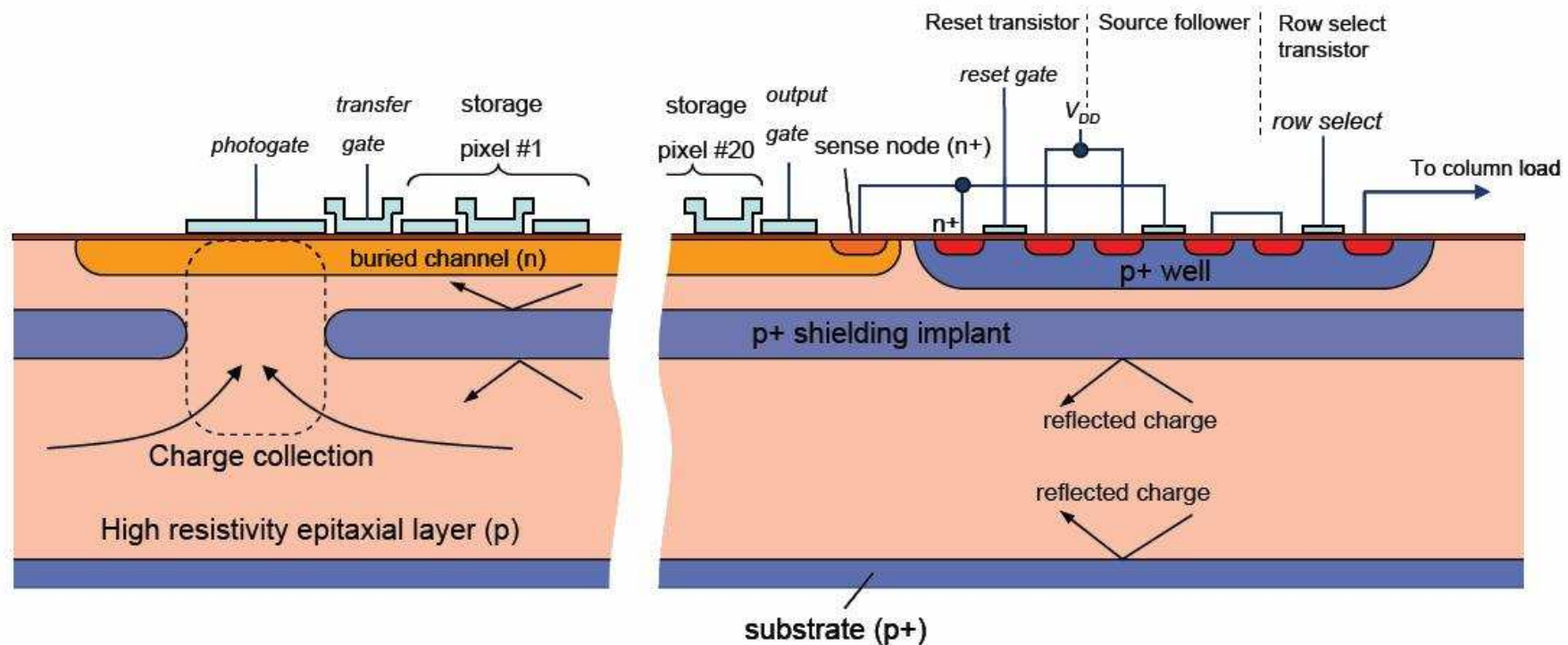
Readout Chips – CPR1 and CPR2



- CPR2 designed for CPC2
- Results from CPR1 taken into account
- Numerous test features
- Size : 6 mm \times 9.5 mm
- 0.25 μm CMOS process (IBM)
- Work in progress to design CPR2A with improved performance

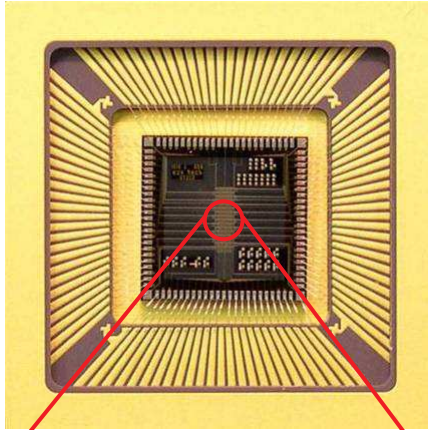
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In-situ Storage Image Sensor : ISIS

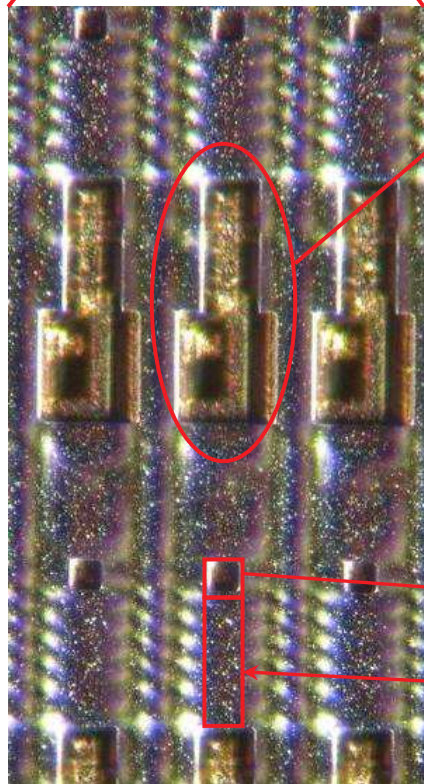


- Charge is collected into a photogate
- Each pixel has its own 20-cell CCD register : store raw charge during collisions
- Increased resistance to EMI
- Column-parallel readout during quiet time at ~1 MHz: much reduced clocking requirements

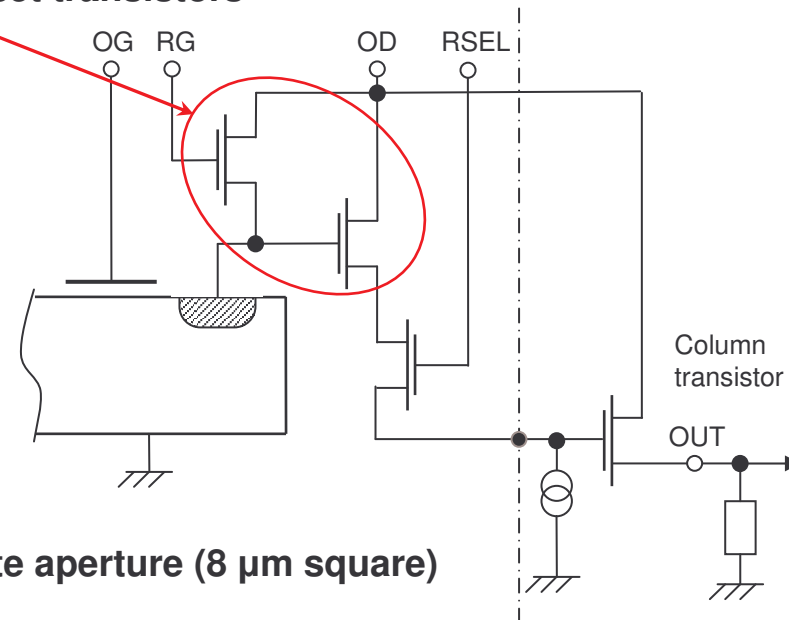
The ISIS1 Cell



- 16×16 array of ISIS cells with 5-pixel buried channel CCD storage register each
- Cell pitch 40 μm × 160 μm, no edge logic (pure CCD process)
- Chip size ≈ 6.5 mm × 6.5 mm



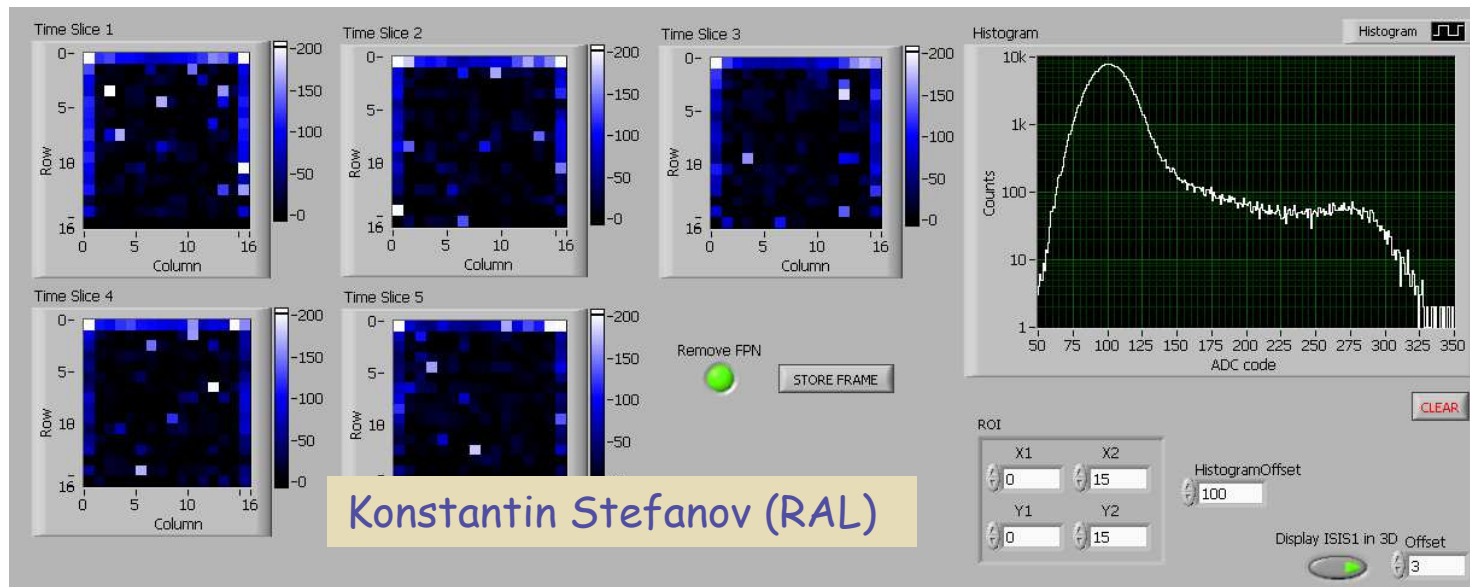
Output and reset transistors



Photogate aperture (8 μm square)

CCD (5×6.75 μm pixels)

Tests of ISIS1



Tests with ^{55}Fe source

- ISIS1 without *p*-well tested first and works OK
- ISIS1 with *p*-well has very large transistor thresholds, permanently off – problem understood and e2V is processing a new batch with *p*-well

Work with 3 other vendors to design ISIS2 with pixel size ~40x50
micron

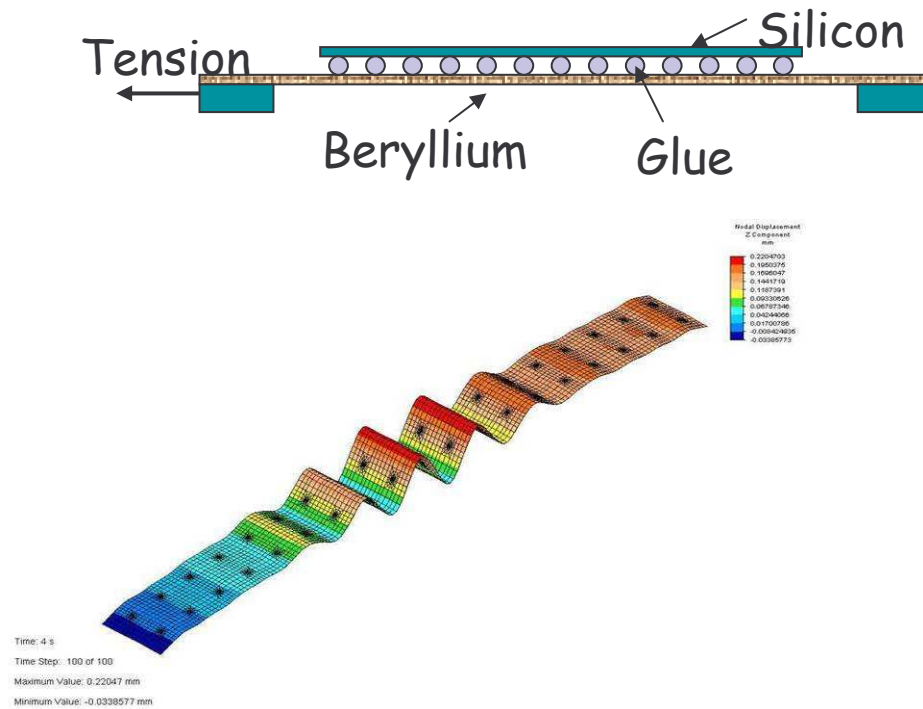
Mechanical Options

Target of 0.1% X_0 per layer (100 μm silicon equivalent)

- **Unsupported Silicon**
 - ◆ Longitudinal tensioning provides stiffness
 - ◆ No lateral stability
 - ◆ Not believed to be promising
- **Thin Substrates**
 - ◆ Detector can be thinned to epitaxial layer (~20 μm)
 - ◆ Silicon glued to low mass substrate for lateral stability
 - ◆ Longitudinal stiffness still from moderate tension
 - ◆ Beryllium has best specific stiffness
- **Rigid Structures**
 - ◆ Foams look very promising

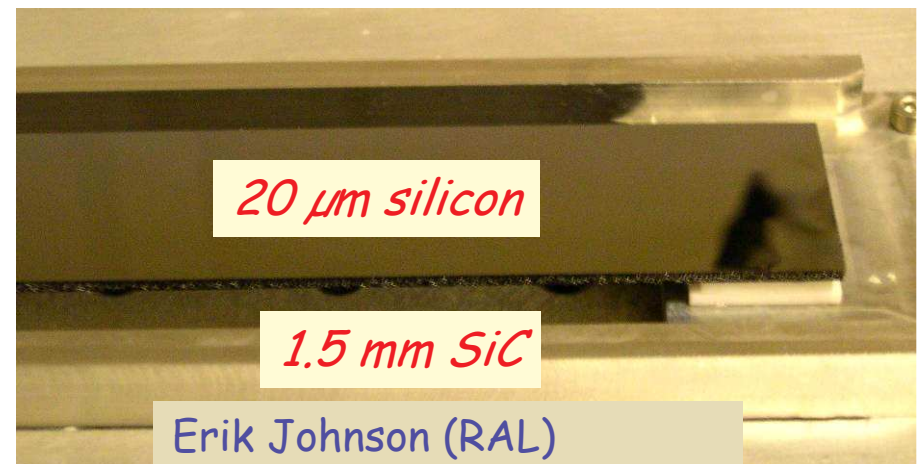
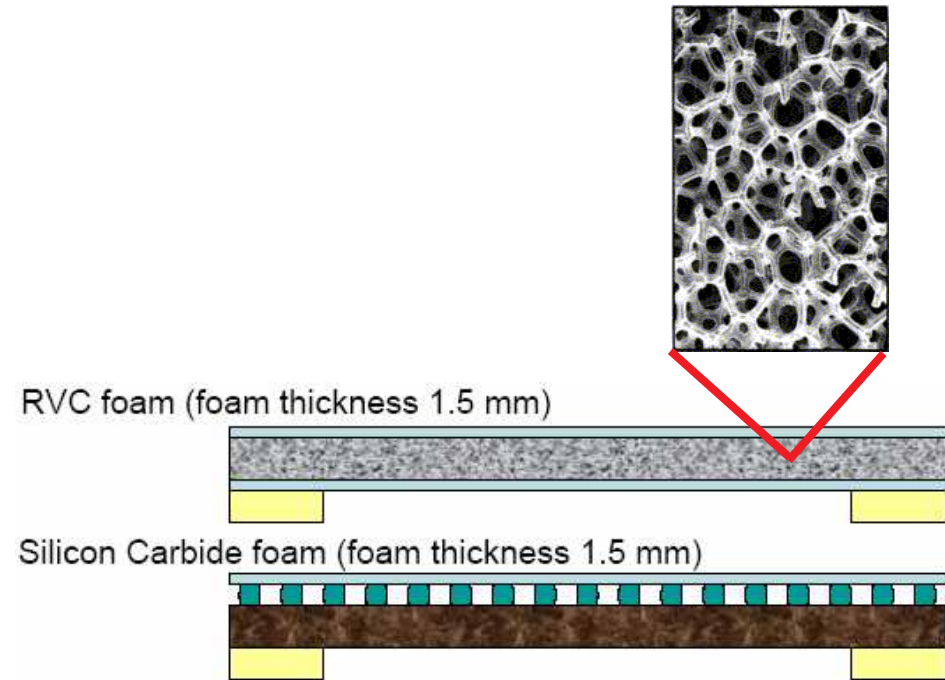
Be and Carbon Fibre Substrates

- Beryllium substrate
 - ◆ Minimum thickness $0.15\% X_0$
 - ◆ Good qualitative agreement from FEA models and measurement
- Carbon Fibre substrate
 - ◆ Better CTE match than Be
 - ◆ $\sim 0.09\% X_0$, no rippling to $<200K$
→ *lateral stability insufficient*



Rigid Structures: Foams

- RVC (Reticulated Vitreous Carbon) and silicon carbide are excellent thermal match to silicon
- Silicon-RVC foam sandwich (~3% density)
 - ◆ Foam (1.5mm thick), sandwiched between two 25 μm silicon pieces – required for rigidity
 - ◆ Achieves 0.09% X0
- Silicon on SiC foam (~ 8% density)
 - ◆ Silicon (25 μm) on SiC foam (1.5mm);
 - ◆ Achieves 0.16% X0
 - ◆ 0.09% X0 possible with lower density foams (< 5%)



LCFI Vertexing and Flavour Tagging Package

- Implementation of ZVTOP algorithm used at SLD
 - ◆ ZVKIN part (ghost track) is implemented as well
- Flavour Tagging Package is using Neural Net based on inputs from the Vertexing Package
- Both packages are fully interfaced to MarlinReco reconstruction framework
 - ◆ Marlin processes exist for all parts of the two packages
- System tests with SGV (fast MC) and MOKKA (full Geant based MC) both give good results
- Documentation is being finalized
- Pilot testing by users has started
- Plan to officially release in April

Summary

- Detector-scale CCDs produced and tested
- First successful readout at 45 MHz
- Demonstrated first sparsified readout with CPR2
- Developed and operated 20A clock driver chip CPD1
- Tested first prototypes of storage devices

- Mechanics : rigid foams favoured as sensor support substrates
- Physics studies : Vertexing and flavour tagging package will be released this month